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File: DWPI

Jun 4, 2004

DERWENT-ACC-NO: 2003-705461
 DERWENT-WEEK: 200465
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*abstract
only*

TITLE: Thermal shut down circuit of semiconductor integrated circuit

INVENTOR: CHOI, S C ; LEE, J H ; OH, W H

PATENT-ASSIGNEE:

ASSIGNEE	CODE
FAIRCHILD KOREA SEMICONDUCTOR CO LTD	FAIH

PRIORITY-DATA: 2001KR-0073829 (November 26, 2001)

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PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
<input type="checkbox"/> KR 434237 B	June 4, 2004		000	H02H005/04
<input type="checkbox"/> KR 2003042942 A	June 2, 2003		001	H02H005/04

APPLICATION-DATA:

PUB-NO	APPL-DATE	APPL-NO	DESCRIPTOR
KR 434237B	November 26, 2001	2001KR-0073829	
KR 434237B		KR2003042942	Previous Publ.
KR2003042942A	November 26, 2001	2001KR-0073829	

INT-CL (IPC): H02 H 5/04

ABSTRACTED-PUB-NO: KR2003042942A

BASIC-ABSTRACT:

NOVELTY - A thermal shut down circuit is provided to measure a chip temperature by arranging a temperature sensing transistor near to a power transistor and covering the power transistor by a metal.

DETAILED DESCRIPTION - At least one or more temperature sensing transistors(11) are installed in a semiconductor integrated circuit so as to be adjacent to thermal sources(31-36) such as power transistors. The temperature sensing transistors are installed corresponding to the power transistors. Alternatively, the temperature sensing transistors are installed between adjacent power transistors. The temperature sensing transistors are covered by a metal line which is contact with the thermal source.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: THERMAL SHUT DOWN CIRCUIT SEMICONDUCTOR INTEGRATE CIRCUIT

DERWENT-CLASS: U11 U13 U24 X13

EPI-CODES: U11-D03; U13-D01; U24-F; X13-C02;

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